

In the Specification:

Please amend paragraph 0018 of the Specification as indicated below.

[0018] The device 100 includes a substrate 101, such as monocrystalline silicon. As the device 100 is an SOI device, a buried oxide layer is disposed over the substrate 101 and is formed by standard fabrication methods. A bulk Si layer 103 is disposed over the SOI layer 102, and is the n⁻-type drift region of the illustrative device 100. A field oxide 104 is disposed over the n⁻-drift layer 103. A p⁻-type body 105 has a p⁺ body contact 106 is formed in contact with the p⁻ body 105. Adjacent to the p⁺ body contact 106 is the n⁺ source 107, which has a source metallization 110 as shown. An n⁺ drain 108 is disposed as shown and has a drain metallization 112 thereover. A field plate 109 is segmented as referenced above, having segments 114 and is illustratively metal, and a gate doped-polysilicon (poly) field plate 111 is similarly segmented, having segments 115. Finally, a dielectric layer 113, such as silicon nitride is disposed beneath the poly field plate 111.

In the Drawings:

Attached please find one drawing sheet, labeled Replacement Sheet 3/3.
Reference numeral 404 has been removed from FIG. 4, no other changes have been made
and no new matter has been added.

Entry of this Drawing Sheet is respectfully requested.